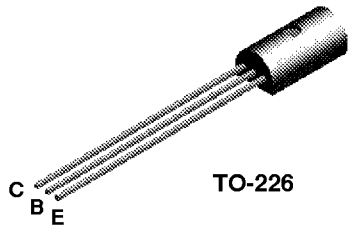
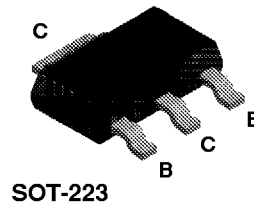


**TN6714A**



**NZT6714**



**NPN General Purpose Amplifier**

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.5 A. Sourced from Process 37.

**Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	2.0	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

**Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		TN6714A	*NZT6714	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	1.0	1.0	W
		8.0	8.0	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	50		°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	125	125	°C/W

\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

# NPN General Purpose Amplifier

(continued)

TN6714A / NZT6714

## Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
<b>OFF CHARACTERISTICS</b>					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \mu\text{A}, I_C = 0$	5.0		V
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = 40 \text{ V}, I_E = 0$		0.1	$\mu\text{A}$
$I_{EBO}$	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		0.1	$\mu\text{A}$

## ON CHARACTERISTICS

$h_{FE}$	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$	55 60 50	250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$		0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$		1.2	V

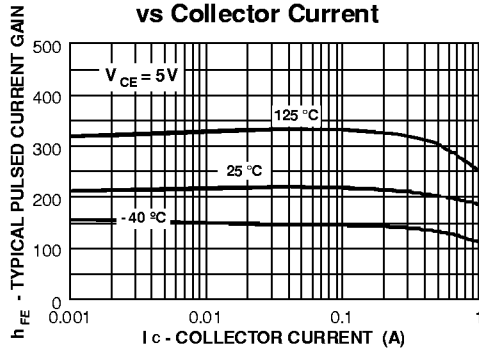
## SMALL SIGNAL CHARACTERISTICS

$h_{fe}$	Small-Signal Current Gain	$I_C = 50 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 20 \text{ MHz}$	2.5	25	
$C_{cb}$	Collector-Base Capacitance	$V_{CB} = 10 \text{ mA}, I_E = 0, f = 1.0 \text{ MHz}$		30	pF

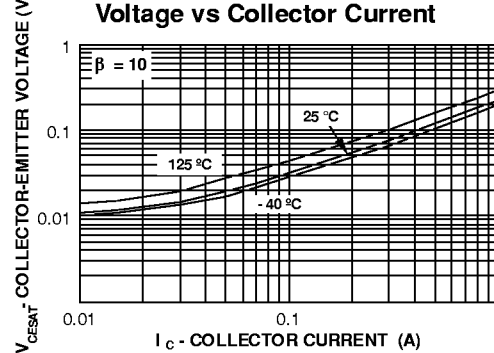
\*Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 1.0\%$

## Typical Characteristics

Typical Pulsed Current Gain vs Collector Current



Collector-Emitter Saturation Voltage vs Collector Current



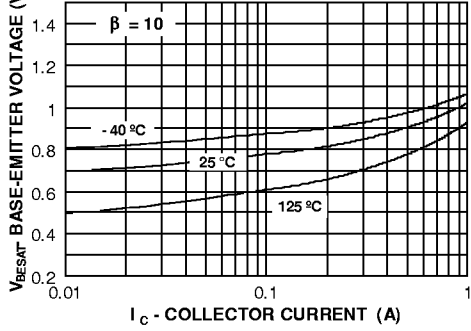
# NPN General Purpose Amplifier

(continued)

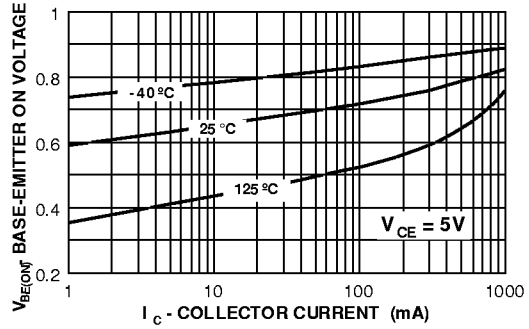
TN6714A / NZT6714

## Typical Characteristics (continued)

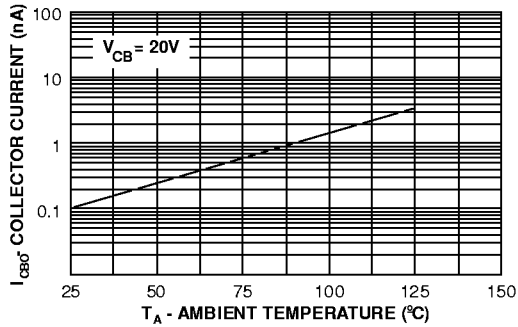
**Base-Emitter Saturation Voltage vs Collector Current**



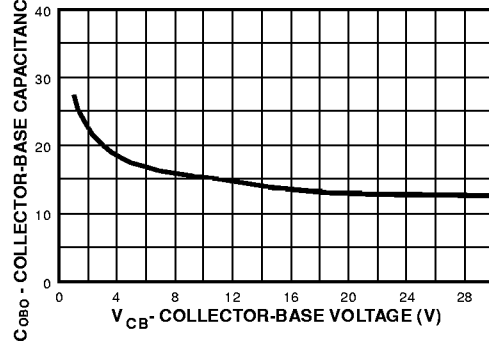
**Base-Emitter ON Voltage vs Collector Current**



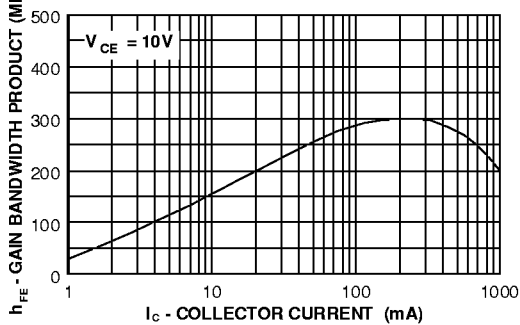
**Collector-Cutoff Current vs Ambient Temperature**



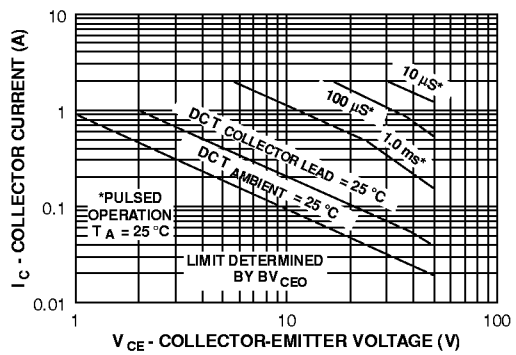
**Collector-Base Capacitance vs Collector-Base Voltage**



**Gain Bandwidth Product vs Collector Current**



**Safe Operating Area TO-226**



Typical Characteristics (continued)

